

IN THE CLAIMS

Cancel claims 15-31 without prejudice or disclaimer, and amend claims 5 and 8 as follows:

1. (Original) A semiconductor device comprising:
surface mounted parts mounted by soldering;
a wiring substrate on which the surface mounted parts are mounted;
solder connection portions for connecting the surface mounted parts to the wiring substrate; and

a sealing portion formed with an elastic insulative resin for covering the surface mounted parts and the solder connection portions,

wherein the elastic resin is a resin having a modulus of elasticity of 200 MPa or less at a temperature of 150°C or higher.

2. (Original) A semiconductor device according to claim 1, wherein the elastic resin is a resin having a modulus of elasticity of 1 MPa or more at a temperature of 150°C or higher.

3. (Original) A semiconductor device according to claim 1, wherein the elastic resin is a resin having a modulus of elasticity of 1 MPa or more at a temperature of 25°C.

4. (Original) A semiconductor device according to claim 1, wherein the elastic resin is a resin having a modulus of elasticity of 200 MPa or more at a temperature of 25°C.

5. (Currently Amendment) A semiconductor device comprising:

surface mounted parts mounted by soldering;

a wiring substrate on which the surface mounted parts are mounted;

Q' solder connection portions for connecting the surface mounted parts to the wiring substrate; and

a sealing portion formed with a silicone resin which is an elastic insulative resin for covering the surface mounted parts and the solder connection portions, wherein the silicone resin has a modulus of elasticity of 200 MPa or less at a temperature of 150°C or higher.

6. (Original) A semiconductor device according to claim 1, wherein the elastic resin is a silicone resin.

7. (Original) A semiconductor device according to claim 1, wherein the elastic resin is an epoxy resin.

8. (Currently Amended) A semiconductor device comprising:

semiconductor chips which are surface mounted parts each formed with a surface electrode at its main surface;

chip parts which are surface mounted parts each formed with connection terminals on both ends;

a module substrate which is a wiring substrate on which the semiconductor chips and the chip parts are mounted;

solder connection portions for connecting the ship parts to the wiring substrate; and

a sealing portion formed with a silicone resin which is an elastic insulative resin for covering the semiconductor chips, the chip parts and the solder connection portions, wherein the silicone resin has a modulus of elasticity of 200 MPa or less at a temperature of 150°C or higher.

9. (Original) A semiconductor device comprising:

semiconductor chips which are surface mounted parts formed with a surface electrode at the main surface;

chip parts which are surface mounted parts each formed with connection terminals on both ends;

a module substrate which is a wiring substrate on which the semiconductor chips and the chip parts are mounted;

solder connection portions for connecting the chip parts to the wiring substrate; and

a sealing portion formed with an insulative resin having a modulus of elasticity of 1 MPa or more and 200 MPa or less at a temperature of 150°C or more and a modulus of elasticity of 200 MPa or more at a temperature of 25°C for covering the semiconductor chips, the chip parts and the solder connection portions.

91 10. (Original) A semiconductor device according to claim 9, wherein the insulative resin is an epoxy resin.

11. (Original) A semiconductor device according to claim 10, wherein chip parts are mounted by soldering to the substrate terminals each formed with a gold plating layer, Sn plating layer or Pb-Sn series solder plating layer at the surface.

12. (Original) A semiconductor device according to claim 11, wherein the surface electrodes of the semiconductor chips are wire bonded by gold wires to the substrate terminals each formed with a gold plating layer, with a Sn plating layer or a Pb-Sn series solder plating layer at the surface.

13. (Original) A semiconductor device according to claim 11, wherein the main surface of the semiconductor chips and the surface of the wiring substrate on the side of supporting the chips are opposed to each other and the surface

a, electrodes of the semiconductor chip and the substrate terminals each formed with a gold metal layer, an Sn plating layer or a Pb-Sn series solder plating layer at the surface are connected by way of gold bumps or solder bumps.

14. (Original) A semiconductor device according to claim 12, wherein the semiconductor chips and the chip parts are mounted on a rectangular module substrate, and the wire loops of the gold wires are formed in the direction parallel with the longitudinal direction of the module substrate.

15-31. (Canceled)
